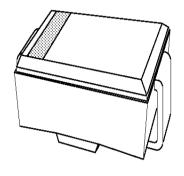
#### DISCRETE SEMICONDUCTORS

# DATA SHEET



# **BYG90-40 series**Schottky barrier rectifier diodes

Product specification
File under Discrete Semiconductors, SC01

1996 May 06





## Schottky barrier rectifier diodes

#### BYG90-40 series

#### **FEATURES**

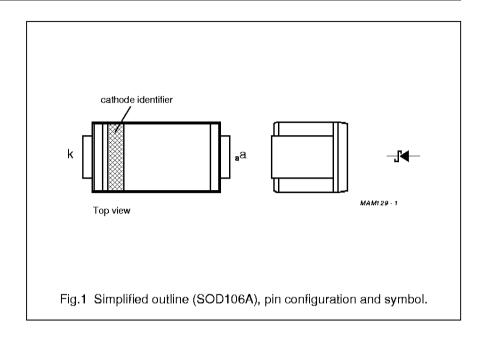
- · Low switching losses
- Capability of absorbing very high surge current
- · Fast recovery time
- · Guard ring protected
- · Plastic SMD package.

#### **APPLICATIONS**

- Low power switched-mode power supplies
- · Rectifying
- · Polarity protection.

#### DESCRIPTION

The BYG 90-40 series consists of Schottky barrier rectifier diodes, fabricated in planar technology, and encapsulated in rectangular SOD106A plastic SMD packages.



Philips Semiconductors Product specification

# Schottky barrier rectifier diodes

BYG90-40 series

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V <sub>R</sub>	continuous reverse voltage				
	BYG90-20		_	20	V
	BYG90-30		_	30	V
	BYG90-40		_	40	V
$V_{RRM}$	repetitive peak reverse voltage				
	BYG90-20		_	20	V
	BYG90-30		_	30	V
	BYG90-40		_	40	V
V <sub>RWM</sub>	crest working reverse voltage				
	BYG90-20		_	20	V
	BYG90-30		_	30	V
	BYG90-40		_	40	V
I <sub>F(AV)</sub>	average forward current	$T_{amb}$ = 65 °C; see Fig.2; $R_{th j-a}$ = 80 K/W; note 1; $V_{R(equiv)}$ = 0.2 V; note 2	_	1	A
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8.3 μs half sine wave; JEDEC method	_	30	Α
I <sub>RSM</sub>	non-repetitive peak reverse current	$t_p = 100  \mu s$	_	0.5	Α
T <sub>stg</sub>	storage temperature		-65	+125	°C
T <sub>i</sub>	junction temperature		_	125	°C

#### Notes

- 1. Refer to SOD106A standard mounting conditions.
- 2. For Schottky barrier diodes thermal run-away has to be considered, as in some applications, the reverse power losses P<sub>R</sub> are a significant part of the total power losses. Nomograms for determination of the reverse power losses P<sub>R</sub> and I<sub>F(AV)</sub> rating will be available on request.

1996 May 06 3

Philips Semiconductors Product specification

# Schottky barrier rectifier diodes

BYG90-40 series

#### **ELECTRICAL CHARACTERISTICS**

 $T_{amb} = 25 \,^{\circ}$ C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per diode						
V <sub>F</sub>	forward voltage	see Fig.2; note 1				
		I <sub>F</sub> = 1 A	_	_	550	mV
		I <sub>F</sub> = 3 A	_	_	850	mV
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 100 °C	_	_	450	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = V <sub>RRMmax</sub> ; note 1; see Fig.3	_	_	1	m <b>A</b>
		$V_R = V_{RRMmax}$ ; $T_j = 100  ^{\circ}\text{C}$ ; note 1; see Fig.3	_	_	10	mA
C <sub>d</sub>	diode capacitance	$V_R = 4 \text{ V}$ ; $f = 1 \text{ MHz}$ ; see Fig.4	_	_	75	pF

#### Note

1. Pulsed test:  $t_p = 300 \ \mu s$ ;  $\delta = 0.02$ .

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	80	K/W

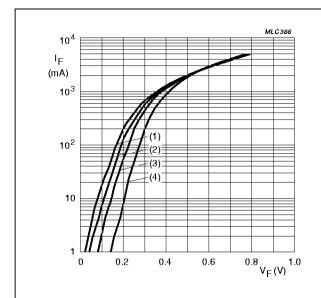
#### Note

1. Refer to SOD106A standard mounting conditions.

# Schottky barrier rectifier diodes

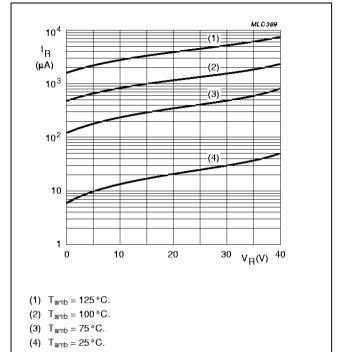
#### BYG90-40 series

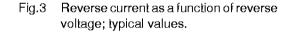
#### **GRAPHICAL DATA**

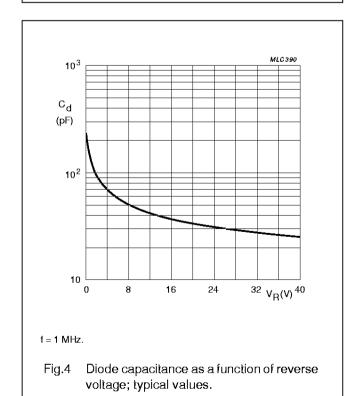


- (1)  $T_{amb} = 125 \,^{\circ}C$ .
- (2)  $T_{amb} = 100 \, ^{\circ}C$ .
- (3)  $T_{amb} = 75 \,^{\circ}C$ .
- (4)  $T_{amb} = 25 \,^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



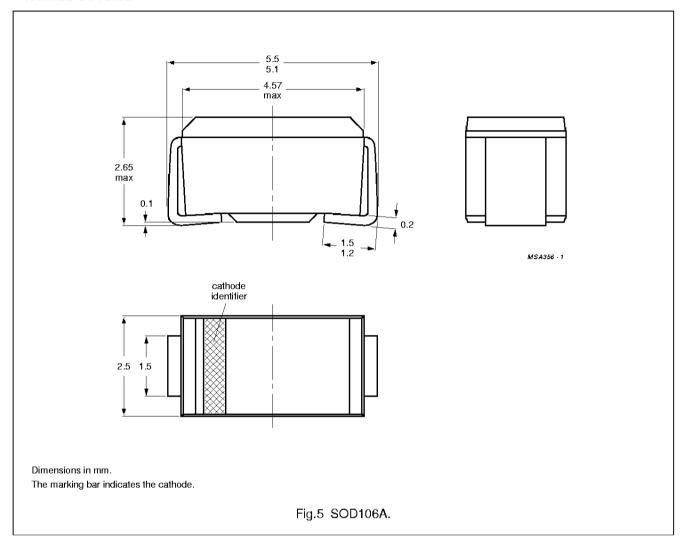




# Schottky barrier rectifier diodes

BYG90-40 series

#### PACKAGE OUTLINE



6

1996 May 06

Philips Semiconductors Product specification

### Schottky barrier rectifier diodes

BYG90-40 series

#### **DEFINITIONS**

Data sheet status				
This data sheet contains target or goal specifications for product development.				
This data sheet contains preliminary data; supplementary data may be published later.				
This data sheet contains final product specifications.				

#### Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### Application information

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

1996 May 06 7